

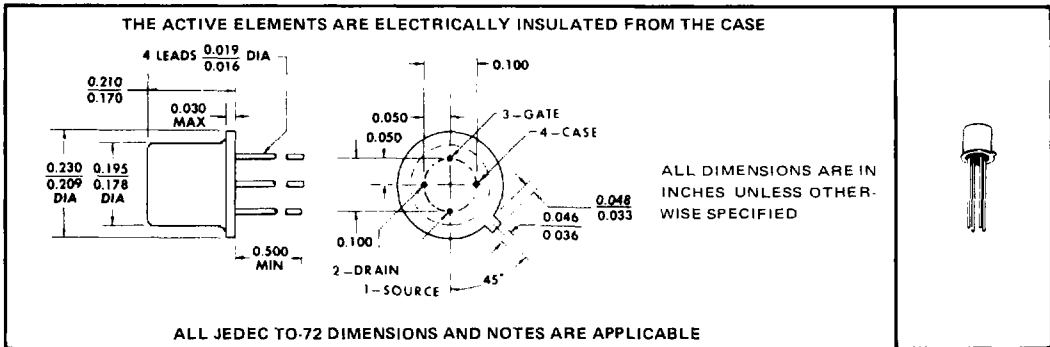
TYPES 2N4416, 2N4416A N-CHANNEL SILICON JUNCTION FIELD-EFFECT TRANSISTORS

BULLETIN NO. DL-S 6810649, JANUARY 1968

FOR VHF AMPLIFIER AND MIXER APPLICATIONS

- High Power Gain . . . 10 dB Min at 400 MHz
- Low Noise Figure . . . 4 dB Max at 400 MHz
- High Transconductance . . . 4000 μ mho Min at 400 MHz
- Low C_{rss} . . . 0.8 pF Max
- High y_{fs}/C_{iss} Ratio (High-Frequency Figure-of-Merit)
- Cross-Modulation Minimized by Square-Law Transfer Characteristic
- Recommended for Use in VHF-UHF Bandpass Amplifiers
- Excellent for General Purpose Amplifier and Chopper Applications

***mechanical data**



4

absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

	2N4416	2N4416A
*Drain-Gate Voltage	30 V	35 V
*Drain-Source Voltage	30 V	35 V
*Reverse Gate-Source Voltage	-30 V	-35 V
*Continuous Forward Gate Current	← 10 mA →	
*Continuous Device Dissipation at (or below) 25°C Free-Air Temperature (See Note 1)	← 300 mW →	
Continuous Device Dissipation at (or below) 125°C Case Temperature (See Note 2)	← 450 mW →	
*Storage Temperature Range	-65°C to 200°C	
*Lead Temperature $\frac{1}{8}$ Inch from Case for 60 Seconds	← 300°C →	

NOTES: 1. Derate linearly to 200°C free-air temperature at the rate of 1.7 mW/°C

2. Derate linearly to 200°C case temperature at the rate of 6 mW/°C.

*Indicates JEDEC registered data

USES CHIP JN53

TYPES 2N4416, 2N4416A

N-CHANNEL SILICON JUNCTION FIELD-EFFECT TRANSISTORS

electrical characteristics at 25°C free-air temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS‡	2N4416		2N4416A		UNIT
		MIN	MAX	MIN	MAX	
$V_{(BR)GSS}$ Gate-Source Breakdown Voltage	$I_G = -1 \mu A, V_{DS} = 0$	-30*		-35*		V
V_{GSF} Gate-Source Forward Voltage	$I_G = 1 \text{ mA}, V_{DS} = 0$		1*		1*	V
I_{GSS} Gate Reverse Current	$V_{GS} = -20 \text{ V}, V_{DS} = 0$		-0.1*		-0.1*	nA
	$V_{GS} = -20 \text{ V}, V_{DS} = 0, T_A = 150^\circ C$		-0.2*		-0.2*	μA
$V_{GS(off)}$ Gate-Source Cutoff Voltage	$V_{DS} = 15 \text{ V}, I_D = 1 \text{ nA}$		-6*		-6*	V
V_{GS} Gate-Source Voltage	$V_{DS} = 15 \text{ V}, I_D = 0.5 \text{ mA}$	-1*	-5.5*	-1*	-5.5*	V
I_{DSS} Zero-Gate-Voltage Drain Current	$V_{DS} = 15 \text{ V}, V_{GS} = 0$, See Note 3	5*	15*	5*	15*	mA
$ Y_{fs} $ Small-Signal Common-Source Forward Transfer Admittance	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 1 \text{ kHz}$	4.5*	7.5*	4.5*	7.5*	mmho
$ Y_{os} $ Small-Signal Common-Source Output Admittance		0.05*	0.05*	0.05*	0.05*	
C_{iss} Common-Source Short-Circuit Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	4*		4*		pF
C_{riss} Common-Source Short-Circuit Reverse Transfer Capacitance		0.8*		0.8*		
C_{oss} Common-Source Short-Circuit Output Capacitance		2*		2*		
$Re(y_{is})$ Small-Signal Common-Source Input Conductance	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 100 \text{ MHz}$	0.1*		0.1*		mmho
$Im(y_{is})$ Small-Signal Common-Source Input Susceptance		2.5*		2.5*		
$Re(y_{os})$ Small-Signal Common-Source Output Conductance		0.075*		0.075*		
$Im(y_{os})$ Small-Signal Common-Source Output Susceptance		1*		1*		
$Re(y_{is})$ Small-Signal Common-Source Input Conductance	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 400 \text{ MHz}$	1*		1*		mmho
$Im(y_{is})$ Small-Signal Common-Source Input Susceptance		10*		10*		
$Re(y_{fs})$ Small-Signal Common-Source Forward Transfer Conductance		4*		4*		
$Re(y_{os})$ Small-Signal Common-Source Output Conductance		0.1*		0.1*		
$Im(y_{os})$ Small-Signal Common-Source Output Susceptance		4*		4*		

NOTE 3: This parameter must be measured using pulse techniques. $t_p = 300 \mu s$, duty cycle $\leq 1\%$.

†Texas Instruments guarantees this value in addition to the JEDEC registered value, which is also shown.

*operating characteristics at 25°C free-air temperature

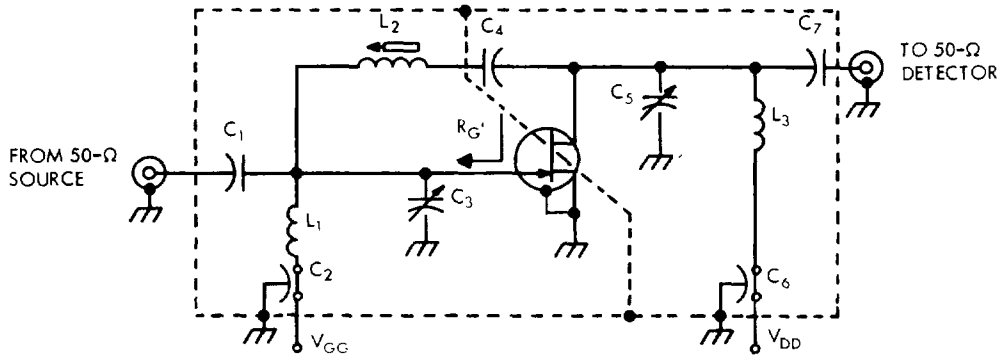
PARAMETER	TEST CONDITIONS‡	MIN	MAX	UNIT
G_{ps} Small-Signal Common-Source Neutralized Insertion Power Gain	$V_{DS} = 15 \text{ V}, I_D = 5 \text{ mA}, f = 100 \text{ MHz}, R_G' = 1 \text{ k}\Omega$, See Figure 1	18		dB
	$V_{DS} = 15 \text{ V}, I_D = 5 \text{ mA}, f = 400 \text{ MHz}, R_G' = 1 \text{ k}\Omega$, See Figure 1	10		
NF Spot Noise Figure	$V_{DS} = 15 \text{ V}, I_D = 5 \text{ mA}, f = 100 \text{ MHz}, R_G' = 1 \text{ k}\Omega$, See Figure 1		2	dB
	$V_{DS} = 15 \text{ V}, I_D = 5 \text{ mA}, f = 400 \text{ MHz}, R_G' = 1 \text{ k}\Omega$, See Figure 1		4	

‡The fourth lead (case) is connected to the source for all measurements.

*Indicates JEDEC registered data

TYPES 2N4416, 2N4416A N-CHANNEL SILICON JUNCTION FIELD-EFFECT TRANSISTORS

PARAMETER MEASUREMENT INFORMATION



CIRCUIT COMPONENT INFORMATION (See Note 4)					
CAPACITORS			COILS		
	100 MHz	400 MHz		100 MHz	400 MHz
C_1	7 pF	1.8 pF			
C_2	0.0015 μ F	0.001 μ F	L_1	0.14 μ H, 3.5 T, #18 enameled copper wire, $\frac{3}{8}$ " I.D., $\frac{1}{4}$ " long	0.022 μ H, $\frac{3}{8}$ " of #16 copper wire formed to 0.5 T, $\frac{1}{4}$ " I.D.
C_3	1-12 pF	0.8-8 pF			
C_4	1000 pF	27 pF	L_2	3 μ H, 17 T, #28 enameled copper wire, close wound, $\frac{9}{32}$ " I.D., powdered iron slug	0.2 μ H, 6 T, #24 enameled copper wire, close wound, $\frac{3}{32}$ " I.D., aluminum slug
C_5	1-12 pF	0.8-8 pF			
C_6	0.0015 μ F	0.001 μ F	L_3	0.25 μ H, 4.5 T, #18 enameled copper wire, $\frac{3}{8}$ " I.D., $\frac{5}{16}$ " long	0.03 μ H, $1\frac{1}{2}$ " of #16 enameled copper wire formed to 1 T, $\frac{3}{8}$ " I.D.
C_7	3 pF	1 pF			

FIGURE 1—NEUTRALIZED POWER GAIN AND SPOT NOISE FIGURE TEST CIRCUIT

NOTE 4 Transformed equivalent source resistance (R_G') is 1000 Ω at 100 MHz for 100-MHz amplifier, and 1000 Ω at 400 MHz for 400-MHz amplifier.

THERMAL INFORMATION

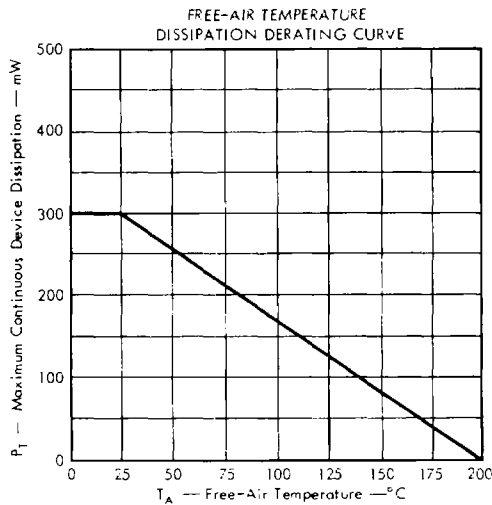


FIGURE 2

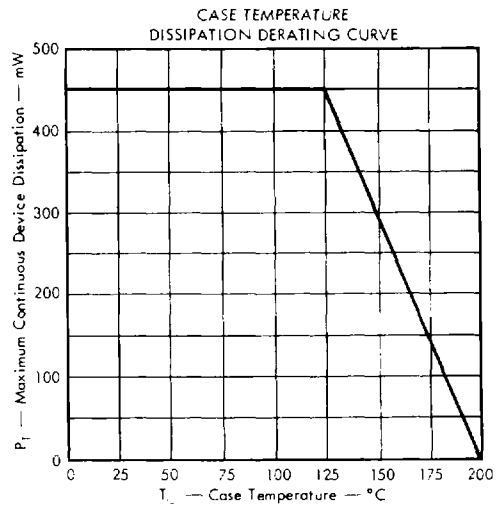


FIGURE 3